



#### SINGLE N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
	7mΩ @ V <sub>GS</sub> = 10V	16A
30V	10mΩ @ V <sub>GS</sub> = 4.5V	13.5A

## **Description**

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Backlighting
- Power Management Functions
- DC-DC Converters

## **Features and Benefits**

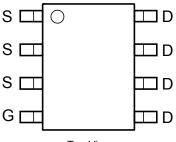
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

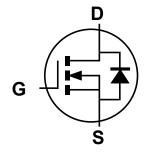
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)







Top View Internal Schematic



Equivalent circuit

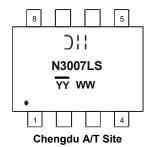
## Ordering Information (Note 4)

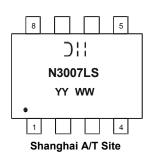
Part Number	Case	Packaging
DMN3007LSS-13	SO-8	2500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**





☐ Nanufacturer's Marking
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☐ Code
☐ YYWW = Date Code Marking
☐ YY or YY = Year (ex: 13 = 2013)
☐ WW = Week (01 - 53)

YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	30	V	
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	16 13	Α
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	64	Α

# Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_{D}$	2.5	W
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	50	°C/W
Operating and Storage Temperature Range	$T_{J_i} T_{STG}$	-55 to +150	°C

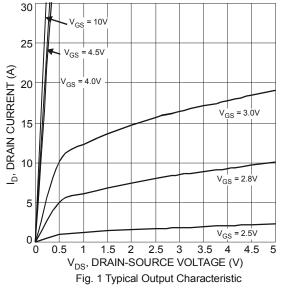
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

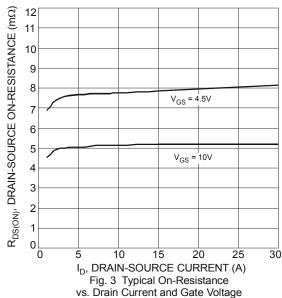
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30		_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_		1	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.3		2.1	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	Б		5	7		V <sub>GS</sub> = 10V, I <sub>D</sub> = 15A	
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	_	7.9	10	mΩ	$V_{GS} = 4.5V, I_D = 13A$	
Forward Transconductance	9 <sub>fs</sub>	_	16.4		S	$V_{DS} = 10V, I_D = 15A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.67	1.2	V	$V_{GS} = 0V, I_S = 2.3A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>		2714		pF	V 45V V 0V	
Output Capacitance	Coss	_	436	_	pF	$V_{DS} = 15V, V_{GS} = 0V$ - f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		380		pF	1 - 1.01/11/12	
Gate Resistance	R <sub>G</sub>		0.7	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
SWITCHING CHARACTERISTICS (Note 8)							
Total Gate Charge	0		31.2			$V_{DS} = 15V$ , $V_{GS} = 4.5V$ , $I_{D} = 16A$	
Total Gate Charge	Qg		64.2	_	nC	$V_{DS} = 15V, V_{GS} = 10V, I_{D} = 16A$	
Gate-Source Charge	Q <sub>gs</sub>	_	7.1	_	IIC	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 16A	
Gate-Drain Charge	Q <sub>gd</sub>	_	17.1	_		V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 16A	
Turn-On Delay Time	t <sub>d(on)</sub>	_	10.3	_			
Rise Time	tr	_	14.8		ns	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V,	
Turn-Off Delay Time	t <sub>d(off)</sub>	_	85.1		115	$I_D = 1A, R_G = 6.0\Omega$	
Fall Time	t <sub>f</sub>	_	43.6	_			

5.Device mounted on 2 oz. Copper pads on FR-4 PCB, with  $R_{\theta JA}$  = +50°C Notes:

6.Pulse width ≤10µS, Duty Cycle ≤1%.
7.Short duration pulse test used to minimize self-heating effect.
8.Guaranteed by design. Not subject to product testing.







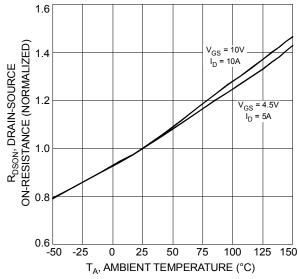
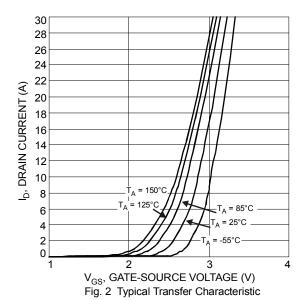


Fig. 5 On-Resistance Variation with Temperature



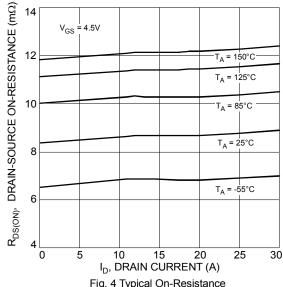


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

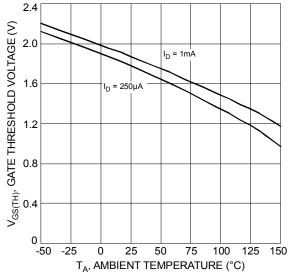
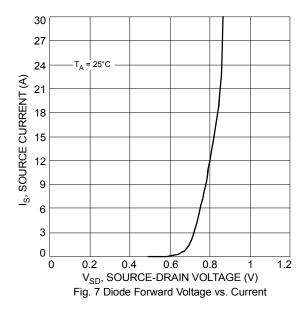
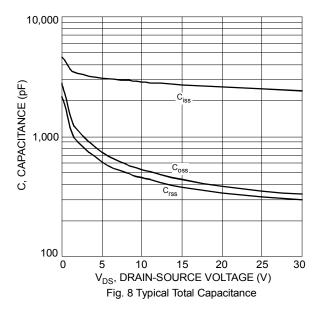
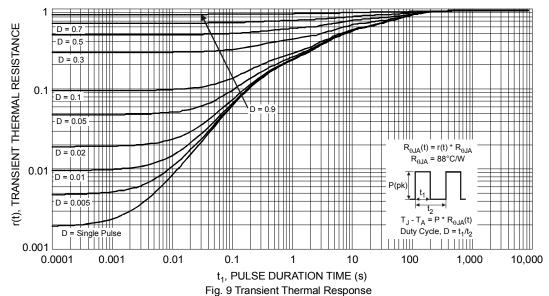


Fig. 6 Gate Threshold Variation vs. Ambient Temperature



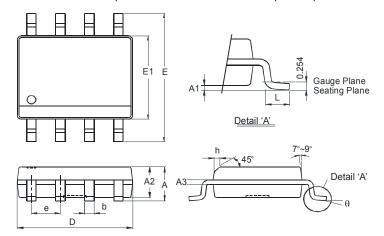






# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version

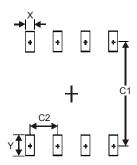


SO-8				
Dim	Min	Max		
Α	I	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
А3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	<b>—</b> 0.35			
Ĺ	0.62	0.82		
θ	θ 0°			
All Dimensions in mm				



## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
X	0.60		
Υ	1.55		
C1	5.4		
C2	1.27		

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